

(54) Title of the invention : SEMICONDUCTOR DEVICE

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(57) Abstract :

This semiconductor device is provided with: a first conductivity type drift layer; a second conductivity type body layer; a first conductivity type source layer; a first conductivity type drain layer; a trench gate that reaches the drift layer by penetrating the body layer; a second conductivity type first semiconductor layer which surrounds a bottom portion of the trench gate and which is isolated from the body layer by means of the drift layer; a first conductivity type second semiconductor layer which is formed along a trench gate end portion in the longitudinal direction of the trench gate and which has one end portion thereof in contact with the body layer and the other end portion thereof in contact with the first semiconductor layer; and a connecting layer which has one end portion thereof connected to the body layer and the other end portion thereof connected to the first semiconductor layer and which is in contact with the second semiconductor layer said connecting layer being isolated from the trench gate end portion in the longitudinal direction of the trench gate by means of the second semiconductor layer.

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